L Number	Hits	Search Text	DB	Time stamp
1	0	(TFT or (thin adj film adj transistor)) and (gate same (poly or polysilicon) same (refractory or W or tungsten or ti or titanium) same taper)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:16
2	11	(TFT or (thin adj film adj transistor)) and (gate same (poly or polysilicon) same (refractory or W or tungsten or ti or titanium)) and (gate same taper)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:23
3	6	("5130772" | "5296729" | "5440168" | "5468986" | "5616933" | "5917225").PN.	USPAT	2004/08/16 10:19
4	289	(TFT or (thin adj film adj transistor)) and (gate same taper)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:23
5	16	((TFT or (thin adj film adj transistor)) and (gate same taper)) and ((polysilicon or poly) same (refractory or W or tungsten or Ti or titanium))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:24
6	16	(((TFT or (thin adj film adj transistor)) and (gate same taper)) and ((polysilicon or poly) same (refractory or W or tungsten or Ti or titanium))) not (("5130772" | "5296729" | "5440168" | "5468986" | "5616933" | "5917225").PN.)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:24
7	5	(((TFT or (thin adj film adj transistor)) and (gate same taper)) and ((polysilicon or poly) same (refractory or W or tungsten or Ti or titanium))) not ((TFT or (thin adj film adj transistor)) and (gate same (poly or polysilicon) same (refractory or W or tungsten or ti or titanium)) and (gate same taper))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:26
8	206	((TFT or (thin adj film adj transistor)) and (gate same taper)) and (gate same tungsten or w or refractory or ti or titanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:49
9	15	((TFT or (thin adj film adj transistor)) and (gate same taper)) and (gate same (tungsten or w or refractory or ti or titanium or cromium or cr or molybdenum or mo)) same (poly or polysilicon or (poly adj silicon))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:50
-	605	(TFT or (thin adj film adj transistor)) and (grain adj size)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/08/16 10:14
-	357	((TFT or (thin adj film adj transistor)) and (grain adj size)) and drain and source and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	2001/12/16 13:03
-	300	(((TFT or (thin adj film adj transistor)) and (grain adj size)) and drain and source and gate) and channel	USPAT; EPO; JPO; DERWENT; IBM_TDB	2001/12/16 13:04
-	33	("Re34658" | "5466619" | "5498904" | "5548132" | "5610737" | "5733793" | "5744824" | "5773329" | "5834797" | "5858820" | "5946562" | "6130120").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/16 14:47
-	78	(bottom adj gate) and ((gate adj electrode) same polysilicon same (tungsten or titanium or w or ti or mo or hf or molybdenum or hafnium))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/01 14:44

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